



DACO SEMICONDUCTOR CO., LTD.

MBRQ601150CT(R)

SCHOTTKY DIODE MODULE TYPE 600A

Features

High Surge Capability
Type 150V V_{RRM}

Maximum Ratings

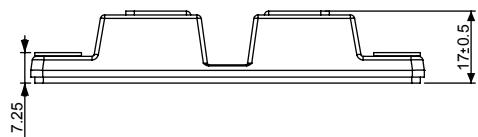
Operating Temperature: -55 °C to +150 °C
Storage Temperature: -55 °C to +150 °C

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
MBRQ601150CT(R)	150V	105V	150V

TWIN TOWER Q

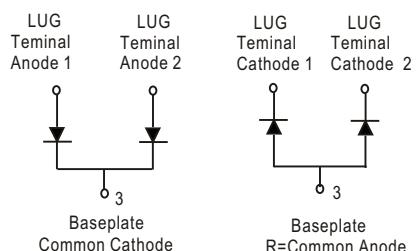
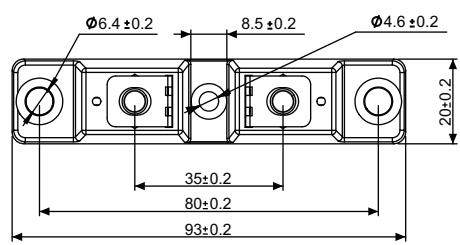


Dimensions in mm (1 mm = 0.0394")



Electrical Characteristics @ 25 °C Unless Otherwise Specified

Average Forward Current (Per pkg)	I _{F(AV)}	600A	T _C =125°C
Peak Forward Surge Current (Per leg)	I _{FSM}	5200A	8.3ms, half sine
Maximum Instantaneous Forward Voltage NOTE(1)	V _F	0.86V	I _{FM} =300A; T _J =25 °C
Maximum Instantaneous Reverse Current At Rated DC Blocking Voltage (Per leg)	I _R	4mA 10mA 50mA	T _J = 25 °C T _J = 100 °C T _J = 150 °C
Maximum Thermal Resistance Junction To Case (Per leg)	R _{θjc}	0.13 °C/W	
Mounting torque		3 ± 0.5Nm 3 ± 0.5Nm	To heatsink To terminals



NOTE :

(1) Pulse Test: Pulse Width 300 μ sec. Duty Cycle < 2%



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